

16-Mbit (2M x 8) MoBL® Static RAM

Features

- **Very high speed**
 - 55 ns
- **Wide voltage range**
 - 2.2V – 3.6V
- **Ultra-low active power**
 - Typical active current: 2 mA @ f = 1 MHz
 - Typical active current: 15 mA @ f = f_{Max} (55 ns Speed)
- **Ultra-low standby power**
- **Easy memory expansion with $\overline{CE_1}$, $\overline{CE_2}$ and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Available in Pb-free and non Pb-free 48-ball VFBGA package**

Functional Description^[1]

The CY62168DV30 is a high-performance CMOS static RAMs organized as 2048Kbit words by 8 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly

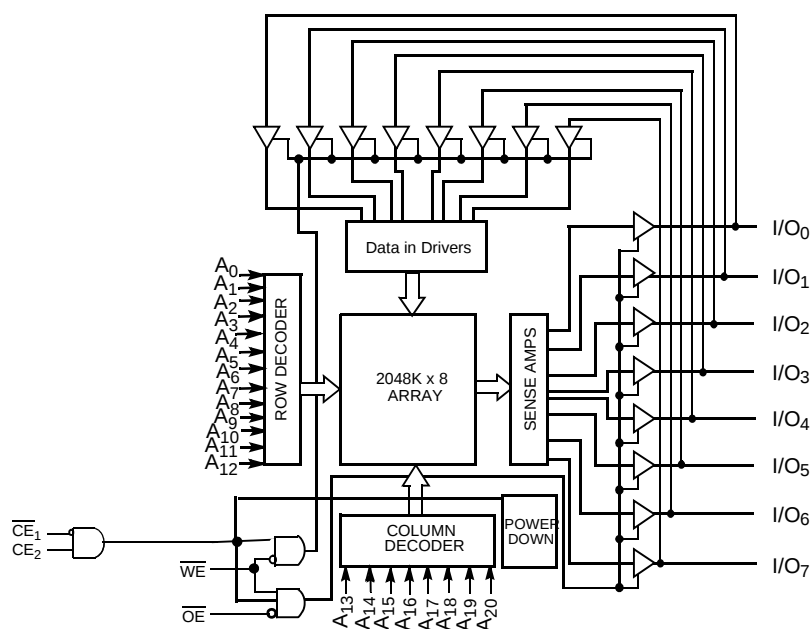
reduces power consumption. The device can be put into standby mode reducing power consumption by 90% when addresses are not toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected Chip Enable 1 ($\overline{CE_1}$) HIGH or Chip Enable 2 ($\overline{CE_2}$) LOW. The input/output pins (I/O₀ through I/O₇) are placed in a high-impedance state when: deselected Chip Enable 1 ($\overline{CE_1}$) HIGH or Chip Enable 2 ($\overline{CE_2}$) LOW, outputs are disabled ($\overline{OE}$ HIGH), or during a write operation (Chip Enable 1 ($\overline{CE_1}$) LOW and Chip Enable 2 ($\overline{CE_2}$) HIGH and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable 1 ($\overline{CE_1}$) LOW and Chip Enable 2 ($\overline{CE_2}$) HIGH and Write Enable ($\overline{WE}$) input LOW. Data on the eight I/O pins (I/O₀ through I/O₇) is then written into the location specified on the address pins (A₀ through A₂₀).

Reading from the device is accomplished by taking Chip Enable 1 ($\overline{CE_1}$) and Output Enable ($\overline{OE}$) LOW and Chip Enable 2 ($\overline{CE_2}$) HIGH while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

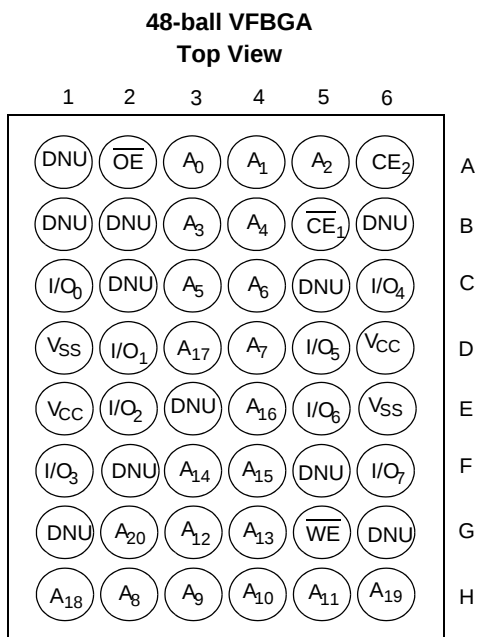
The eight input/output pins (I/O₀ through I/O₇) are placed in a high-impedance state when the device is deselected ($\overline{CE_1}$ LOW and $\overline{CE_2}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE_1}$ LOW and $\overline{CE_2}$ HIGH and $\overline{WE}$ LOW). See the truth table for a complete description of read and write modes.

Logic Block Diagram



Note:

1. For best-practice recommendations, please refer to the Cypress application note entitled *System Design Guidelines*, available at <http://www.cypress.com>.

Pin Configuration^[2]

Product Portfolio

Product	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I _{CC} (mA)				Standby I _{SB2} (μA)	
	f = 1 MHz		f = f _{Max}							
	Min.	Typ. ^[3]	Max.		Typ. ^[3]	Max.	Typ. ^[3]	Max.	Typ. ^[3]	Max.
CY62168DV30LL	2.2	3.0	3.6	55	2	4	15	30	2.5	22

Notes:

2. DNU pins have to be left floating or tied to V_{SS} to ensure proper operation.

3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with
Power Applied -55°C to +125°C

Supply Voltage to Ground
Potential -0.3V to $V_{CC(max)}$ + 0.3V

DC Voltage Applied to Outputs
in High-Z State^[4, 5] -0.3V to $V_{CC(max)}$ + 0.3V

DC Input Voltage^[4, 5] -0.3V to $V_{CC(max)}$ + 0.3V

Output Current into Outputs (LOW) 20 mA

Static Discharge Voltage > 2001V
(per MIL-STD-883, Method 3015)

Latch-up Current > 200 mA

Operating Range

Range	Ambient Temperature (T_A) ^[6]	V_{CC} ^[7]
Industrial	-40°C to +85°C	2.2V – 3.6V

DC Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions	CY62168DV30-55			Unit
			Min.	Typ. ^[3]	Max.	
V_{OH}	Output HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OH} = -0.1 \text{ mA}$	2.0		V
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OH} = -1.0 \text{ mA}$	2.4		
V_{OL}	Output LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$	$I_{OL} = 0.1 \text{ mA}$		0.4	V
		$2.7V \leq V_{CC} \leq 3.6V$	$I_{OL} = 2.1 \text{ mA}$		0.4	
V_{IH}	Input HIGH Voltage	$2.2V \leq V_{CC} \leq 2.7V$		1.8	$V_{CC} + 0.3$	V
		$2.7V \leq V_{CC} \leq 3.6V$		2.2	$V_{CC} + 0.3$	
V_{IL}	Input LOW Voltage	$2.2V \leq V_{CC} \leq 2.7V$		-0.3	0.6	V
		$2.7V \leq V_{CC} \leq 3.6V$		-0.3	0.8	
I_{IX}	Input Leakage Current	$GND \leq V_I \leq V_{CC}$		-1	+1	μA
I_{OZ}	Output Leakage Current	$GND \leq V_O \leq V_{CC}$, Output disabled		-1	+1	μA
I_{CC}	V_{CC} Operating Supply Current	$f = f_{Max} = 1/t_{RC}$	$V_{CC} = 3.6V$, $I_{OUT} = 0 \text{ mA}$, CMOS level		15	mA
		$f = 1 \text{ MHz}$			2	
I_{SB1}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, $V_{IN} \leq 0.2V$, $f = f_{Max}$ (Address and Data Only), $f = 0$ (OE, WE)		2.5	22	μA
I_{SB2}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, $f = 0$, $V_{CC} = 3.6V$		2.5	22	μA

Capacitance^[8]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{CC} = V_{CC(typ.)}$	8	pF
C_{OUT}	Output Capacitance		10	pF

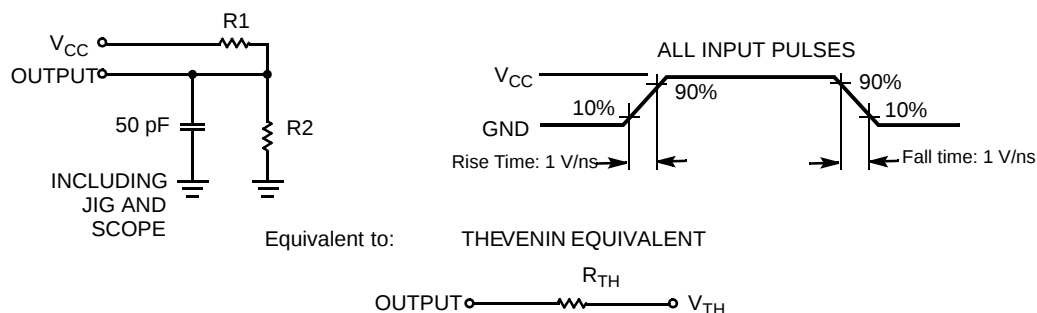
Notes:

- $V_{IL(min)}$ = -2.0V for pulse durations less than 20 ns.
- $V_{IH(max)}$ = $V_{CC} + 0.75V$ for pulse durations less than 20 ns.
- T_A is the "Instant-On" case temperature.
- Full device AC operation assumes a 100 μs ramp time from 0 to $V_{CC(min)}$ and 100 μs wait time after V_{CC} stabilization.
- Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance^[8]

Parameter	Description	Test Conditions	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, 2-layer printed circuit board	55	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		16	°C/W

AC Test Loads and Waveforms

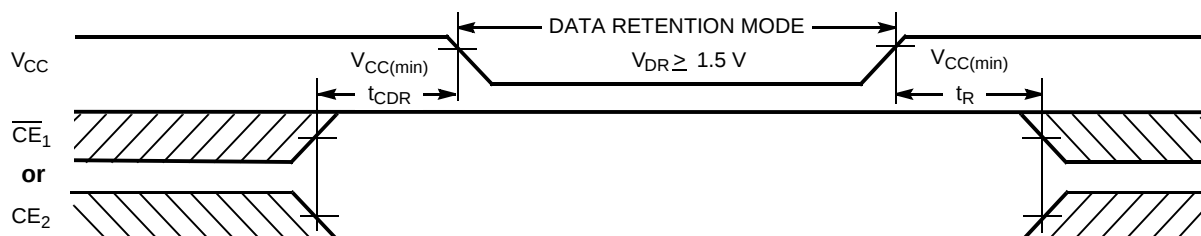


Parameters	2.5V	3.0V	Unit
R1	16600	1103	Ω
R2	15400	1554	Ω
R _{TH}	8000	645	Ω
V _{TH}	1.2	1.75	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ. ^[3]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.5		3.6	V
I _{CCDR}	Data Retention Current	V _{CC} = 1.5V CE ₁ ≥ V _{CC} - 0.2V or CE ₂ ≤ 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V			10	μA
t _{CDR} ^[8]	Chip Deselect to Data Retention Time		0			ns
t _R ^[9]	Operation Recovery Time		t _{RC}			ns

Data Retention Waveform



Note:

9. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} ≥ 100 μs or stable at V_{CC(min.)} ≥ 100 μs.

Switching Characteristics Over the Operating Range ^[10]

Parameter	Description	55 ns		Unit
		Min.	Max.	
Read Cycle				
t _{RC}	Read Cycle Time	55		ns
t _{AA}	Address to Data Valid		55	ns
t _{OHA}	Data Hold from Address Change	10		ns
t _{ACE}	$\overline{CE}_1$ LOW and CE ₂ HIGH to Data Valid		55	ns
t _{DOE}	$\overline{OE}$ LOW to Data Valid		25	ns
t _{LZOE}	$\overline{OE}$ LOW to Low Z ^[11]	5		ns
t _{HZOE}	$\overline{OE}$ HIGH to High Z ^[11, 12]		20	ns
t _{LZCE}	$\overline{CE}_1$ LOW and CE ₂ HIGH to Low Z ^[11]	10		ns
t _{HZCE}	$\overline{CE}_1$ HIGH or CE ₂ LOW to High Z ^[11, 12]		20	ns
t _{PU}	$\overline{CE}_1$ LOW and CE ₂ HIGH to Power-Up	0		ns
t _{PD}	$\overline{CE}_1$ HIGH or CE ₂ LOW to Power-Down		55	ns
Write Cycle ^[13]				
t _{WC}	Write Cycle Time	55		ns
t _{SCE}	$\overline{CE}_1$ LOW and CE ₂ HIGH to Write End	40		ns
t _{AW}	Address Set-Up to Write End	40		ns
t _{HA}	Address Hold from Write End	0		ns
t _{SA}	Address Set-Up to Write Start	0		ns
t _{PWE}	$\overline{WE}$ Pulse Width	40		ns
t _{SD}	Data Set-Up to Write End	25		ns
t _{HD}	Data Hold from Write End	0		ns
t _{HZWE}	$\overline{WE}$ LOW to High Z ^[11, 12]		20	ns
t _{LZWE}	$\overline{WE}$ HIGH to Low Z ^[11]	10		ns

Notes:

10. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3ns or less (1V/ns), timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section.

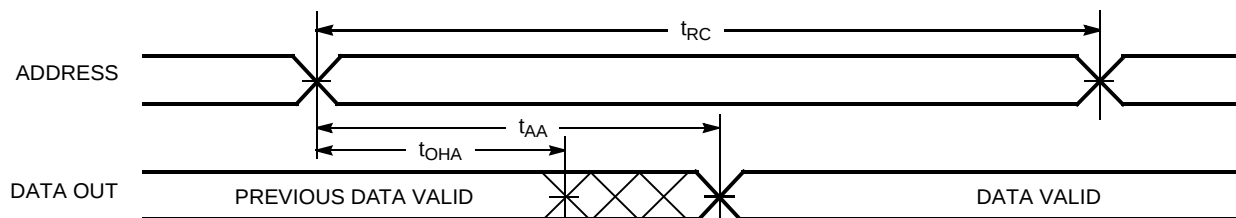
11. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.

12. t_{HZOE} , t_{HZCE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.

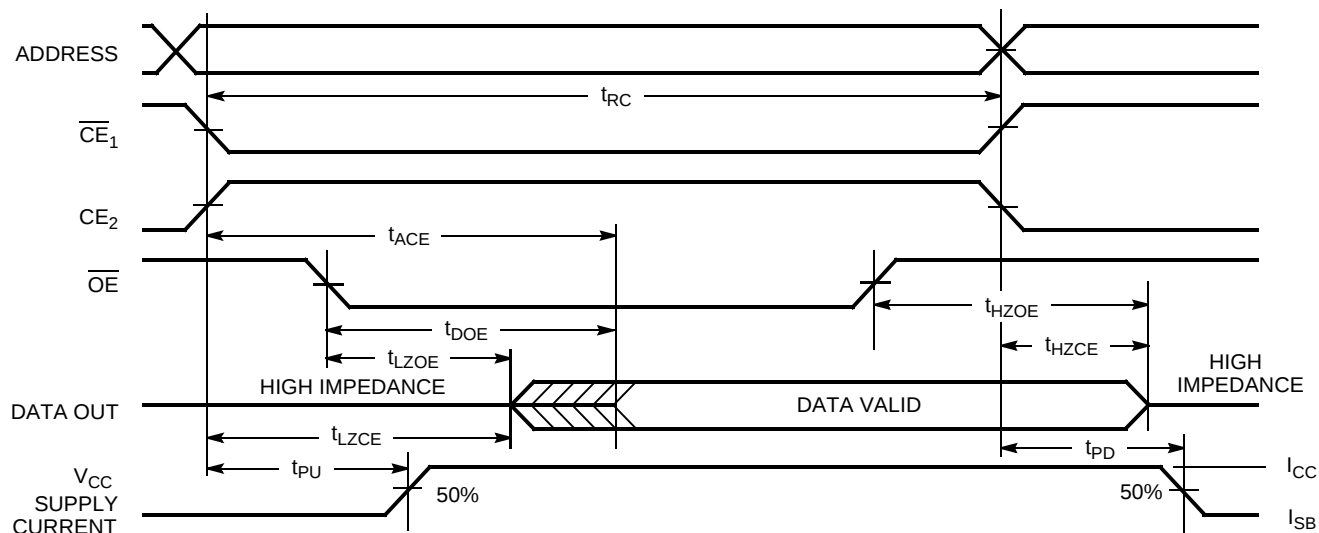
13. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $CE_1 = V_{IL}$, and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

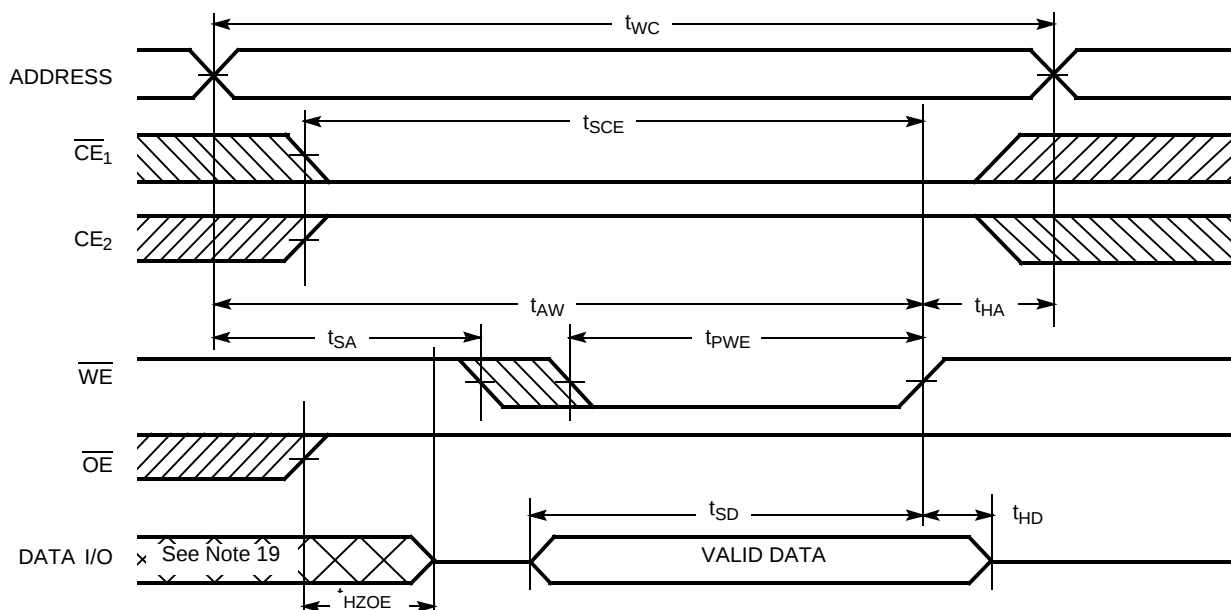
Read Cycle No. 1 (Address Transition Controlled)^[14, 15]



Read Cycle No. 2 ($\overline{\text{OE}}$ Controlled)^[15, 16]



Write Cycle No. 1 ($\overline{\text{WE}}$ Controlled)^[13, 17, 18]

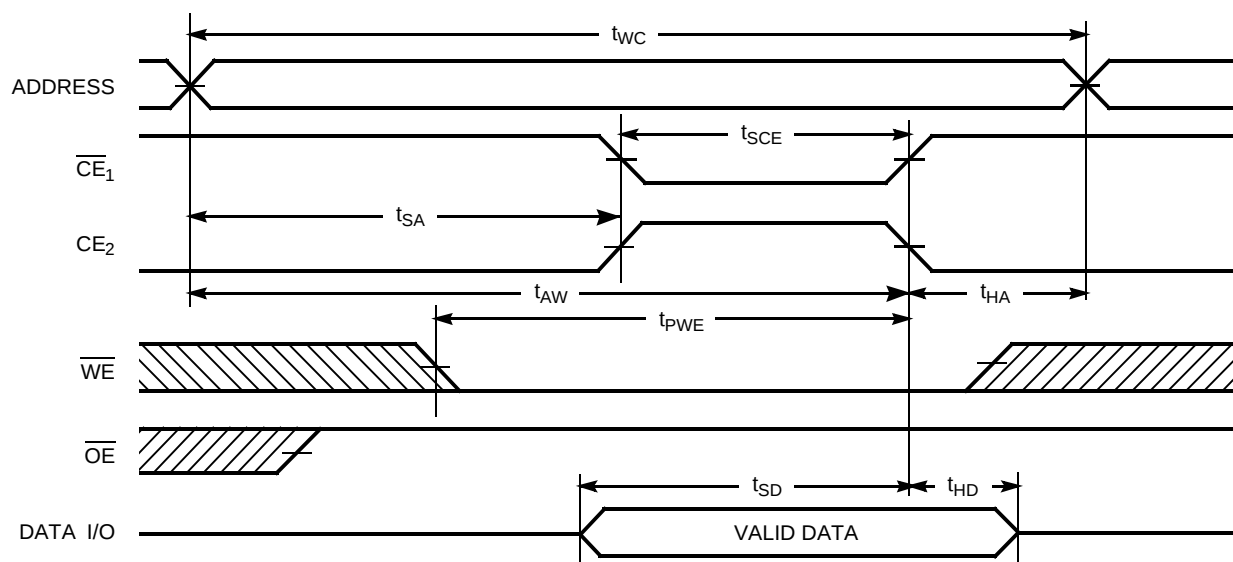


Notes:

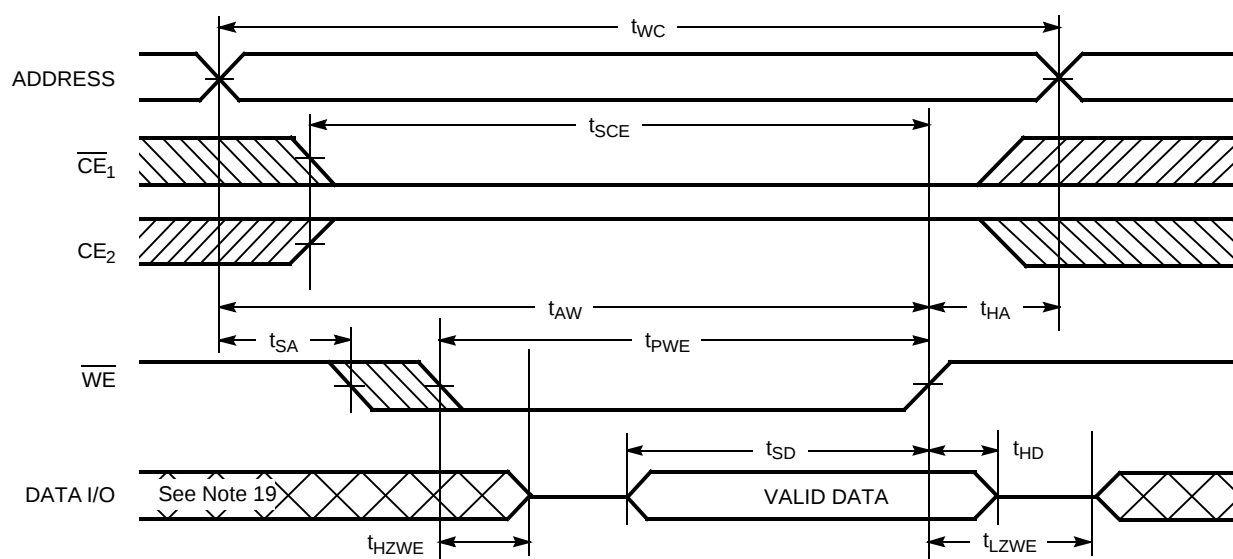
14. Device is continuously selected. $\overline{\text{OE}}$, $\overline{\text{CE}}_1 = V_{IL}$, $\text{CE}_2 = V_{IH}$.
15. $\overline{\text{WE}}$ is HIGH for read cycle.
16. Address valid prior to or coincident with $\overline{\text{CE}}_1$ transition LOW and CE_2 transition HIGH.
17. Data I/O is high impedance if $\overline{\text{OE}} = V_{IH}$.
18. If $\overline{\text{CE}}_1$ goes HIGH or CE_2 goes LOW simultaneously with $\overline{\text{WE}}$ HIGH, the output remains in high-impedance state.
19. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE}_1$ or $\overline{CE}_2$ Controlled)^[13, 17, 18]



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)^[19]



Truth Table

$\overline{CE}_1$	$\overline{CE}_2$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	Data Out (I/O ₀ -I/O ₇)	Read	Active (I_{CC})
L	H	L	X	Data in (I/O ₀ -I/O ₇)	Write	Active (I_{CC})
L	H	H	H	High Z	Output Disabled	Active (I_{CC})

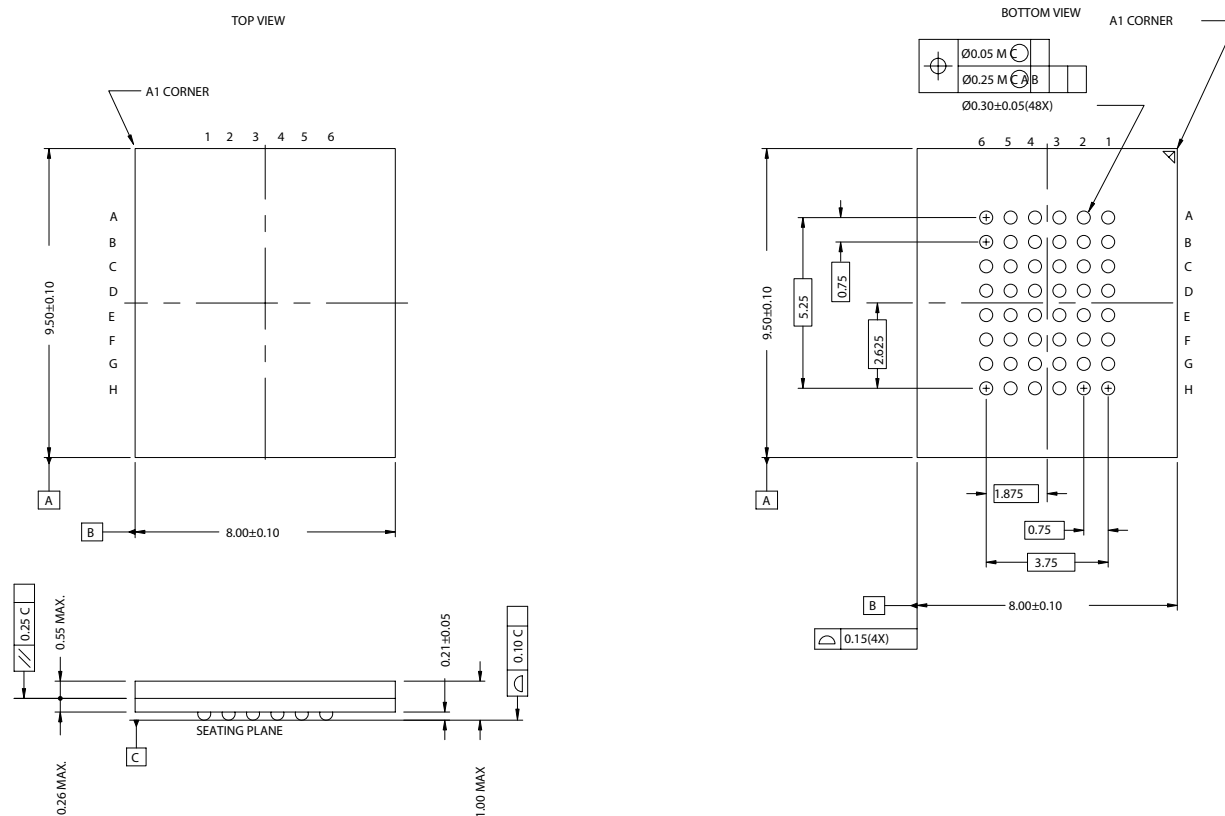
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62168DV30LL-55BVI	51-85178	48-ball Fine Pitch BGA (8 x 9.5 x 1 mm)	Industrial
	CY62168DV30LL-55BVXI		48-ball Fine Pitch BGA (8 x 9.5 x 1 mm) (Pb-free)	

Please contact your local Cypress sales representative for availability of these parts

Package Diagram

48-ball VFBGA (8 x 9.5 x 1 mm) (51-85178)



51-85178-**

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Document History Page

Document Title: CY62168DV30 MoBL [®] , 16-Mbit (2M x 8) MoBL [®] Static RAM Document Number: 38-05329				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	118409	09/30/02	GUG	New Data Sheet
*A	123693	02/05/03	DPM	Changed Advance Information to Preliminary Added package diagram
*B	126556	04/24/03	DPM	Minor change: Change sunset owner from DPM to HRT
*C	132869	01/15/04	XRJ	Changed Preliminary to Final
*D	272589	See ECN	PCI	Updated Final data sheet and added Pb-free package.
*E	335864	See ECN	PCI	Removed redundant packages from Ordering Information Table Added Address A ₂₀ to ball G2 in the Pin Configuration
*F	492895	See ECN	VKN	Changed address of Cypress Semiconductor Corporation on Page# 1 from "3901 North First Street" to "198 Champion Court" Removed 70 ns speed bin Removed L power bin from product offering Updated Ordering Information Table